REMARKS

Prior to the present response, claims 1-69 were pending. By way of the above amendments, claims 1, 10 and 43 are amended. Claims 1-69 currently are pending, with claims 59-63 being withdrawn from consideration.

Applicant again notes with appreciation the Examiner's allowance of claims 19-42, 51-58, 66-67 and 69, and his indication that claims 8, 9, 17, 18, 48 and 49 contain allowable subject matter. It is respectfully submitted, however, that all pending claims in the present application are in condition for allowance, for the reasons advanced below.

Independent claims 1 and 10 are amended to recite that the first insulating film is formed to cover an entire surface of the channel forming region, and claim 43 is amended to recite that the first insulating film is formed to cover an entire surface of the first region and an entire surface of the second region. Support for these features is found in Figures 1D, 2D, 3D, or 4D, for example. The amendment to claim 43 also broadens the claim in some respects and recites that the first region overlaps with the gate electrode, with the first insulating film and the second insulating film interposed therebetween, and does not overlap with the first auxiliary electrode, which is shown, for example, in Figures 3D or 4D.

The Office Action includes a rejection of claims 1, 4-7, 10, 13-16, 43, 46, 47, 50, 64, 65 and 68 under 35 U.S.C. § 102 as allegedly being anticipated by Ogura et al. (U.S. Patent No. 6,255,166), and a rejection of claims 2, 3, 11, 12, 44 and 45 under 35 U.S.C. § 103 as allegedly being obvious over the Ogura et al. patent. To the extent that the Office may consider these rejections to apply to the amended claims, Applicant respectfully traverses.

As pointed out above, independent claims 1 and 10 now recite, among other features, that the first insulating film is formed to cover an entire surface of the channel forming region. It is respectfully submitted that the Ogura et al. patent neither discloses nor suggests this feature in combination with the other features of the independent claims.

With reference to Figure 13, the Examiner asserts that Ogura et al. shows a channel forming region 211, 212 and a first insulating film 132a. However, the insulating film 132a of Ogura et al. appears to be provided only at a portion below the gate electrode 242R, and thus it does not cover an entire surface of the channel region 211. Hence, Ogura et al does not teach or suggest the claimed feature of a "first insulating film is formed to cover an entire surface of the channel forming region."

Amended claim 43 recites *inter alia* that the first insulating film is "formed to cover an entire surface of the first region and an entire surface of the second region," and that "the first region overlaps with the gate electrode with the first insulating film and the second insulating film interposed therebetween, and does not overlap with the first auxiliary electrode" to further clarify the positional relationship between the claimed "first region," "second region," "gate electrode" and "auxiliary electrode." At page 4 of the Office Action, the Examiner asserts that the claimed "first region" corresponds to a portion of 212R of Ogura et al. directly under 131c and adjacent region 211, the claimed "second region" corresponds to another portion of 212R adjacent drain region 222, the claimed "first insulating film" corresponds to the insulating film 132a and the claimed "second insulating film" corresponds to the insulating film 131c. However, the portion of region 212R relied upon for meeting the claimed "first portion" overlaps with gate electrode 242R, and thus cannot meet the claimed feature of "the first region ... does not overlap with the first auxiliary electrode."

The invention as set forth in the amended claims facilitates controlling a thickness of an insulating film between the gate electrode and a channel forming region in a semiconductor film, and a thickness of an insulating film between the semiconductor film and an auxiliary electrode. For example, the total thickness of the insulating films between the channel forming region and the gate electrode can be formed with a predetermined thickness, which is thicker than the thickness of an insulating film between the semiconductor film and an auxiliary electrode, to have a high withstand voltage, as described in page 9, line 28 through page 10, line 5 of the specification. The insulating films 132 of Ogura et al., by contrast, is provided below the gate electrodes 242 and does not cover the channel region 211. Thus, the Ogura et al. patent not only fails to teach or suggest all the claim limitations, but it also fails to suggest flexibilities provided by the claimed invention.

For at least these reasons, the Ogura et al. patent fails to teach or suggest the each and every feature in combinations of features set forth in independent claims 1, 10 and 43. Accordingly, claims 1, 10 and 43, and the claims depending therefrom, are patentable.

Based on the foregoing, it is respectfully submitted that the present application is in condition for allowance, and prompt notification of the same is earnestly sought.

Respectfully submitted,

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